

COVALENT METROLOGY

Welcome



PHOTO-INDUCED FORCE MICROSCOPY (PIFM): AUGMENTING SURFACE ANALYSIS WITH AFM CHEMICAL MAPPING

Sung Park, PhD Cofounder and CEO, Molecular Vista Graceson Aufderheide Applications Engineer, Molecular Vista

July 27, 2023 | 11am PT



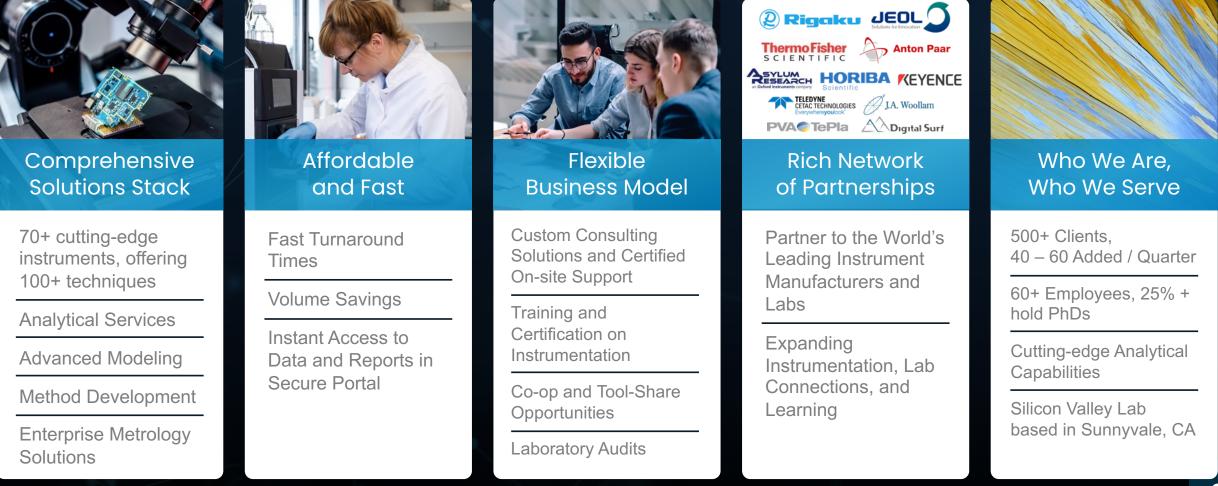


COVALENT ACADEMY

Industrial Applications of Advanced Metrology Episode 35



Silicon Valley-based analytical labs and platform delivering quality data and expert analysis for advanced materials and device innovation



Covalent Analytical Services



4

PCBA, Semiconductor, and Electronic Device Metrology & Failure Analysis	Electron Microscopy and Scanning Probe Microscopy	Optical Microscopy & Spectroscopy	X-Ray Characterization
 DPA / Mechanical Cross-section Dye & Pry Test EBIC / OBIC failure analysis Hot Spot Detection IR Imaging / Emission Microscopy NIR Imaging Root-Cause Failure Analysis 	 AFM & Advanced AFM Modes (EFM, KPFM, MFM, PFM) Scanning Acoustic Microscopy (SAM) SEM (+ EDS) FIB-SEM (+ EDS) S/TEM (+ EDS / + EELS) Nano-indent / Nano-scratch 	 Chromatic Aberration Digital Optical Microscopy FTIR and ATR-FTIR Laser Scanning Confocal Microscopy Spectral Ellipsometry UV-Vis-NIR Spectroscopy White Light Interferometry 	 X-Ray Diffraction (XRD) X-Ray Reflectometry (XRR) Micron-spot ED-XRF WDXRF Micro-computed X-ray Tomography (Micro-CT) 2D X-ray Inspection & X-ray Radiography
Elemental / Chemical Composition Analysis	Particle Analysis	Material Property Characterization	Surface Spectroscopy Analysis
 EPMA GD-OES GC-MS ICP-MS and LA-ICP-MS Raman Microscopy & Spectroscopy NMR (1D or 2D; solid / liquid) 	 Dynamic Light Scattering (DLS) Laser Diffraction Particle Size Analysis (PSA) Particle Zeta Potential 	 DSC DMA & TMA Rheometry TGA Solid Surface Zeta Potential Porometry / Porosity Gas Adsorption Gas Pycnometry Foam Density Tap Density 	 Dynamic-SIMS ToF-SIMS (Static-SIMS) Ion Scattering Spectroscopy (ISS) Ultraviolet Photoelectron Spectroscopy (UPS) X-ray Photoelectron Spectroscopy (XPS)

Covalent Partners



Today's webinar is in partnership with



- Team of Experts behind:
 - Photo-Induced Force Microscopy (PiFM)
 - Photo-Induced Force IR Spectroscopy (PiFIR)
- Techniques enable mapping and analyzing the chemistry of smaller volumes than ever before.
- Collaboration with Covalent brings these solutions to new applications and supports advanced device & materials research.



Introducing



Dr. Sung Park

Co-founder and CEO, Molecular Vista



- Received a PhD in Applied Physics from Stanford University in 1986.
- After graduating, he worked for almost 2 decades developing new scientific instrumentation specializing in advanced technologies for atomic force microscopy.
- In 2012, he co-founded Molecular Vista to empower analysts to probe and understand matter at the molecular level through quantitative visualization.





Infrared Photo-induced Force Microscopy

July 27, 2023 Sung Park sung@molecularvista.com

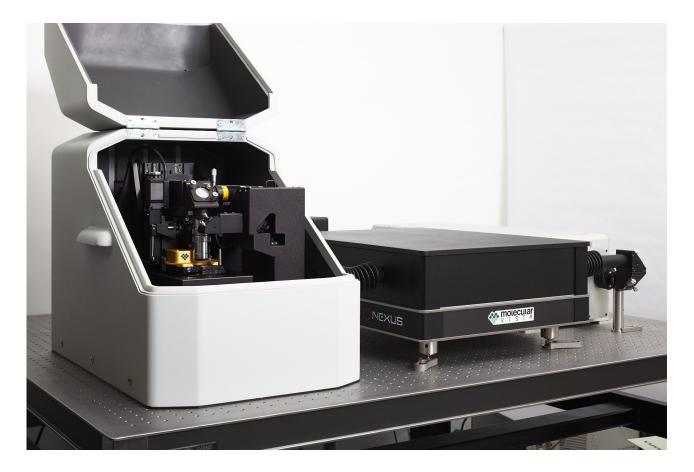
Complements other Nanoscale Analytical Techniques

	IR PiFM	Raman	FTIR	TOF-SIMS	XPS	TXRF	SEM/EDS	TEM	Auger
Species Detected		M.I.	M.I.	M.I.	M.I.	E.I.	E.I.	E.I.	E.I.
Chemical Mapping		Yes	Yes	Yes	Yes	Yes (Elemental)	Yes (Elemental)	Yes (Elemental)	Yes
Lateral Resolution		>0.5 μm	> 10 µm	>0.2 μm	10 μm – 2 mm	~ 1 mm	1 nm* 0.5μm EDS	0.2 nm* 1 ~ 20 nm EDS	~ 10 nm
Depth Probed		> 500 nm	1 µm	1 nm	10 nm	10 nm	1 µm	~ 100 nm	10 nm
	* Ir	maging	M.I. Molecular information			E.I. Elemental information			

IR PiFM brings molecular analysis to the realm of true nanoscale, providing both IR absorption spectra and chemical mapping with ~ 5 nm spatial resolution and monolayer sensitivity.



IR PiFM on Vista AFM Platform

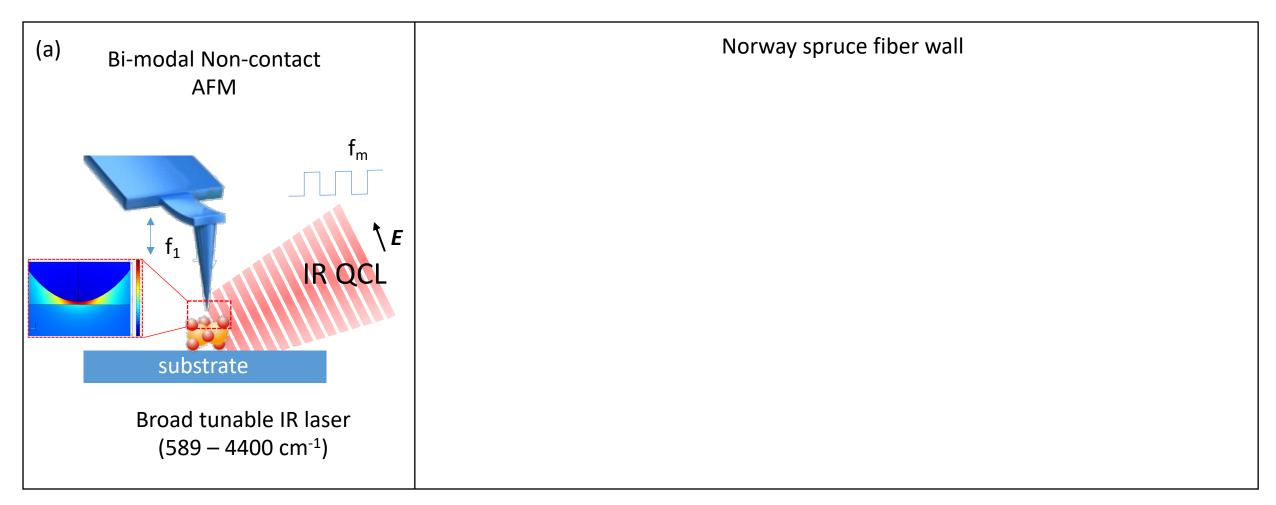


Vista 75

- Sample Size: 4" diameter x 1" height
- Scan Range: 80 x 80 x 12 μm^3
- AFM + multiple laser sources
- IR PiFM + other optional near-field techniques
- If a sample can be analyzed via AFM, IR PiFM is possible
- Vista One and Vista 200 also available



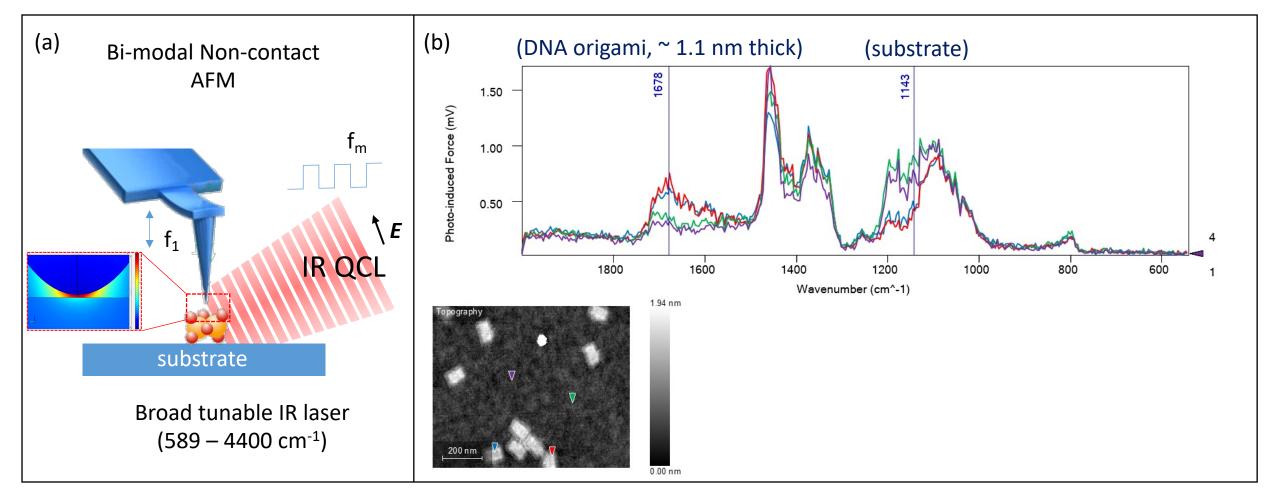
Infrared Photo-induced force microscope (IR PiFM)





Infrared Photo-induced force microscope (IR PiFM)

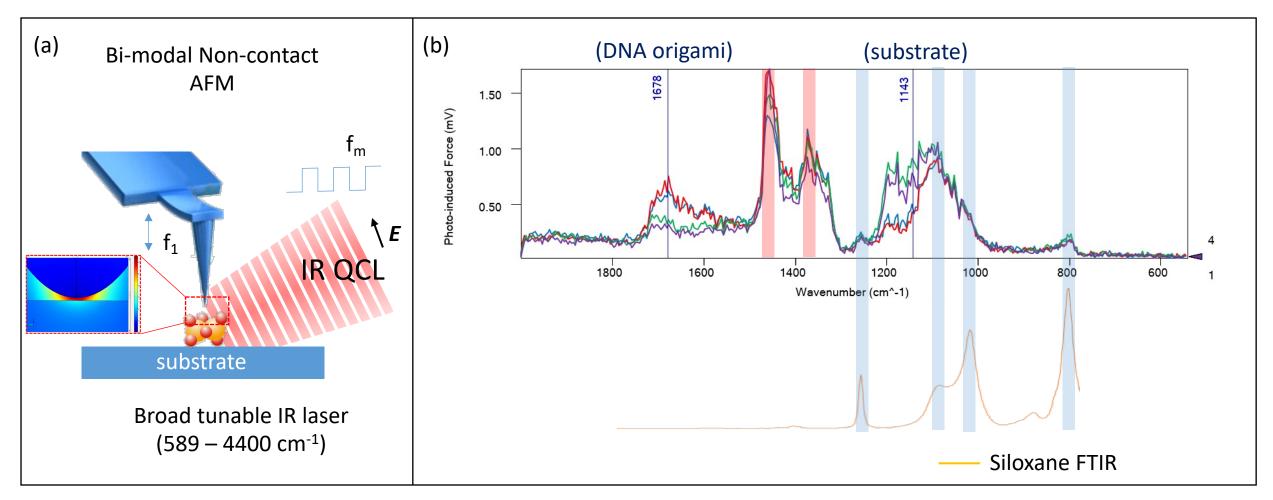
Monolayer Sensitivity





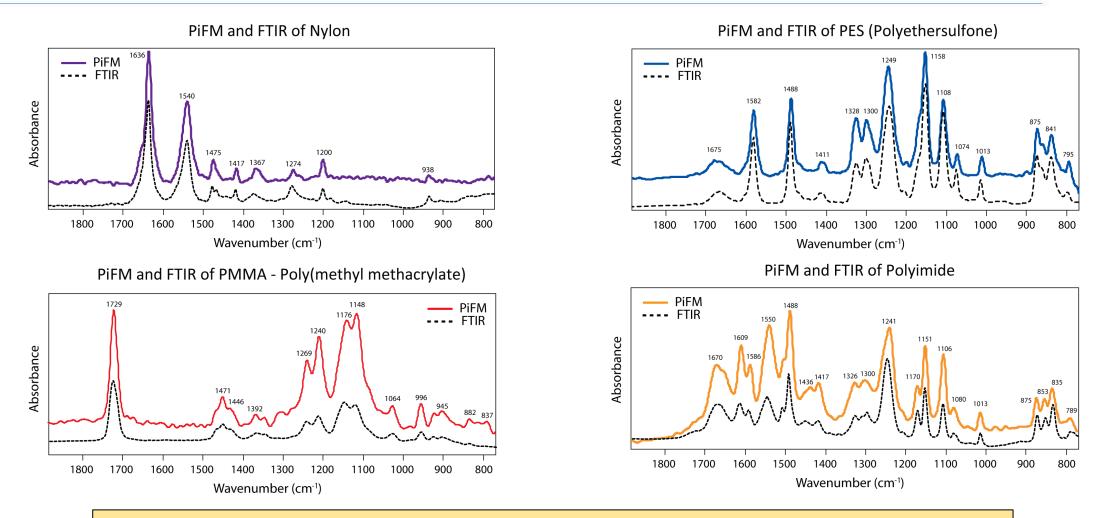
Infrared Photo-induced force microscope (IR PiFM)

Monolayer Sensitivity





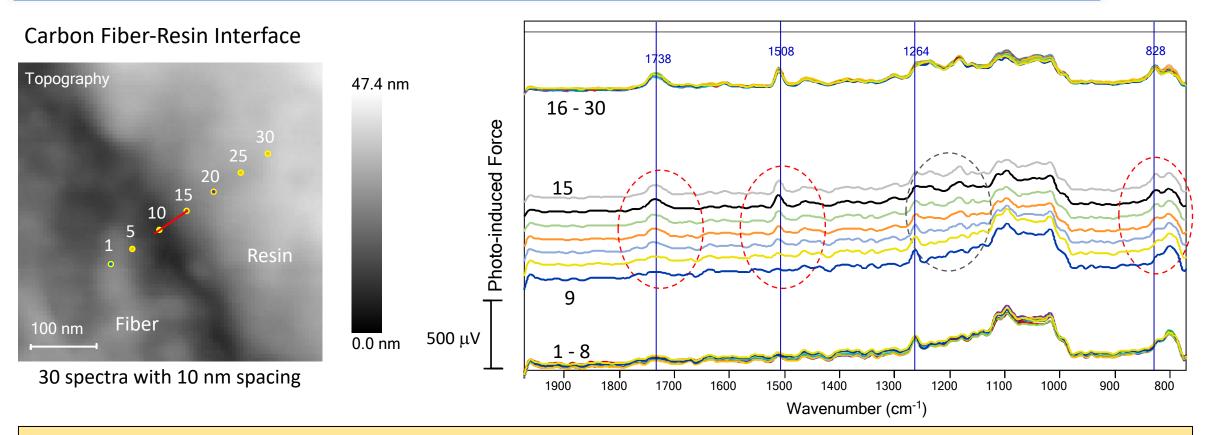
Excellent Agreement between Nanoscale PiF-IR and FTIR Spectra



Excellent agreement between PiF-IR spectra (originating from ~ 5 nm region) and FTIR spectra (originating from ~ 10 μ m region) on homogeneous samples.



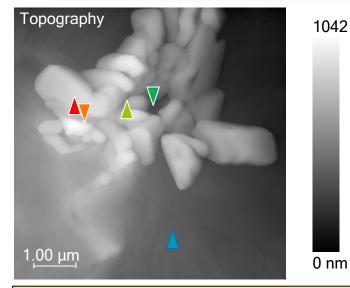
Excellent Repeatability



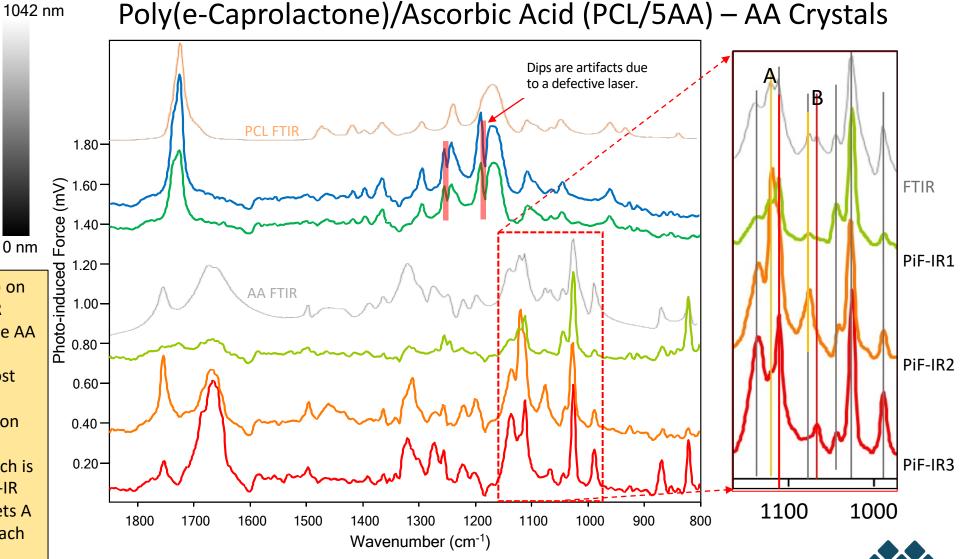
The interface between a carbon fiber and resin are analyzed by preparing a cross-section of the composite fiber via microtome. 30 PiF-IR spectra are acquired across the interface with ~ 10 nm spacing. The first 8 spectra in the carbon fiber and the last 16 - 30 spectra are very repeatable, with all the spectral changes taking place over 9 - 15 spectra. The SNR is good enough to discern chemical changes for each 10 nm changes in spatial location.



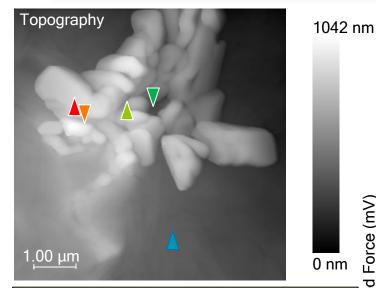
Discrimination of Molecular Orientation



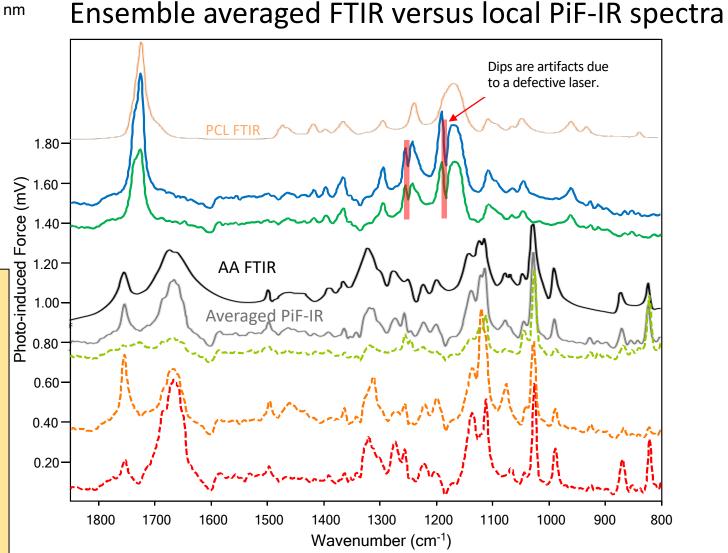
The two spectra (blue and dark green) on homogeneous PCL match the PCL FTIR well. The three spectra acquired on the AA crystals show different peak strengths compared to the AA FTIR. PiF-IR is most sensitive to modes that are out of the sample plane. As such, PiF-IR spectra on different crystal orientations highlight different peaks compared to FTIR, which is an ensemble average of billions of PiF-IR spectra. Note that for the FTIR doublets A and B, the red and orange spectrum each showcase different singlets.



Discrimination of Molecular Orientation

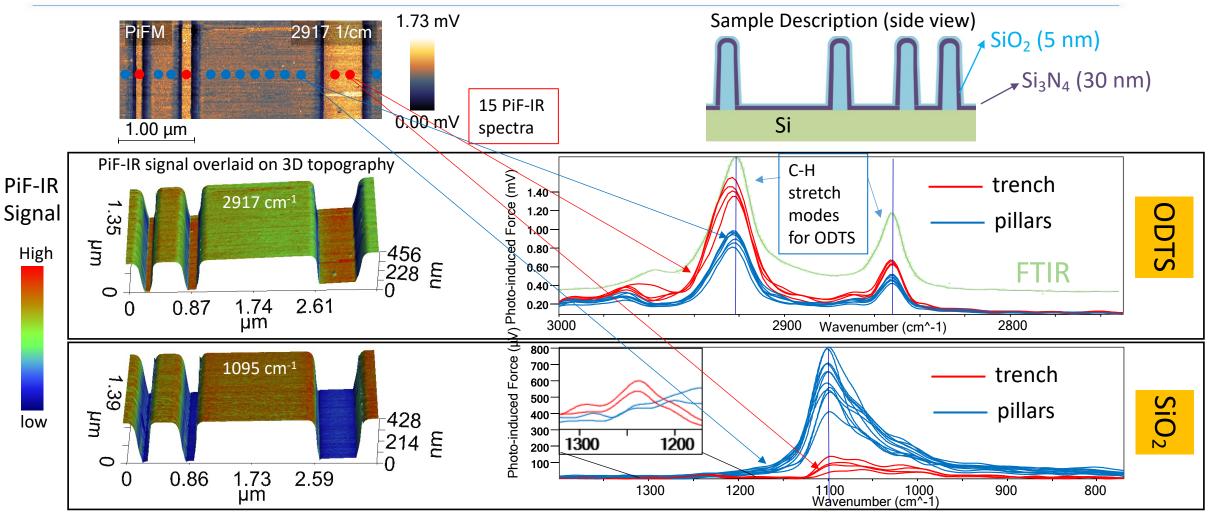


The two spectra (blue and dark green) on homogeneous PCL match the PCL FTIR well. The three spectra acquired on the AA crystals show different peak strengths compared to the AA FTIR. PiF-IR is most sensitive to modes that are out of the sample plane. As such, PiF-IR spectra on different crystal orientations highlight different peaks compared to FTIR, which is an ensemble average of billions of PiF-IR spectra. Note that for the FTIR doublets A and B, the red and orange spectrum each showcase different singlets.





ODTS on SiO₂ (Organic & Inorganic Films)

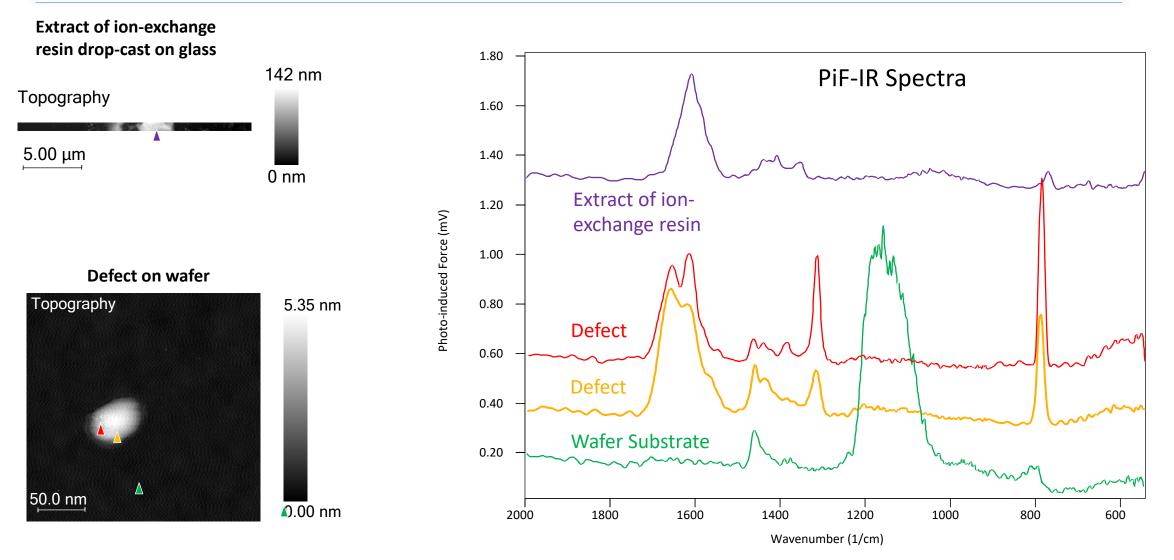


Octadecyltrichlorosilane (ODTS) molecules are self-assembled on top of a 5nm-thick SiO_2 . ODTS SAM layer is thin enough that PiF-IR spectra for the SiO_2 (bottom panel) can be acquired through the SAM layer. Note that the spectra for SiO_2 are different for the pillars (blue) and trenches (red), indicating different forms of SiO_2 . As a results, higher packing density of ODTS (upper panel) is observed for the trenches.

Defects and Residue

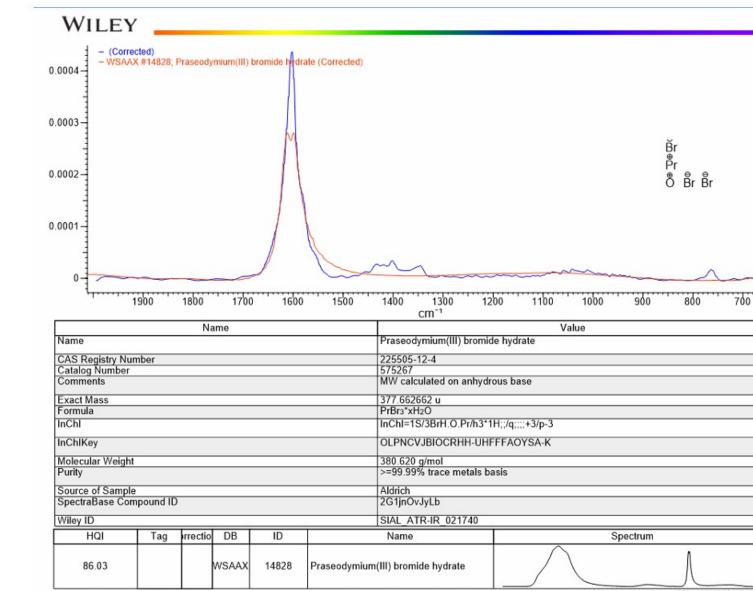


Defect/Residue on Wafer Processed by Ultrapure Water





One Component Search - Resin



About Cobalt(II) Bromide Hydrate

Most metal bromide compounds are water soluble for uses in water treatment, chemical analysis and in ultra high purity for certain crystal growth applications.

American Elements

H

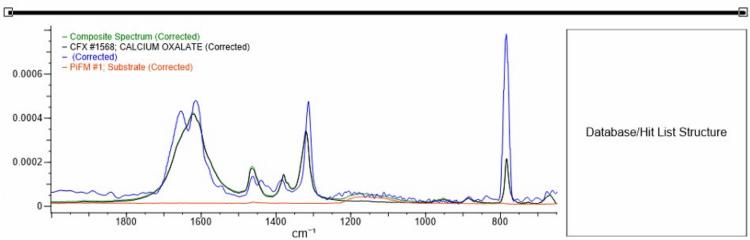
https://www.americanelements.com > cobalt-ii-bromide-h...

Cobalt(II) Bromide Hydrate | AMERICAN ELEMENTS ®



Two Components Search – Defect (red spectrum)

WILEY

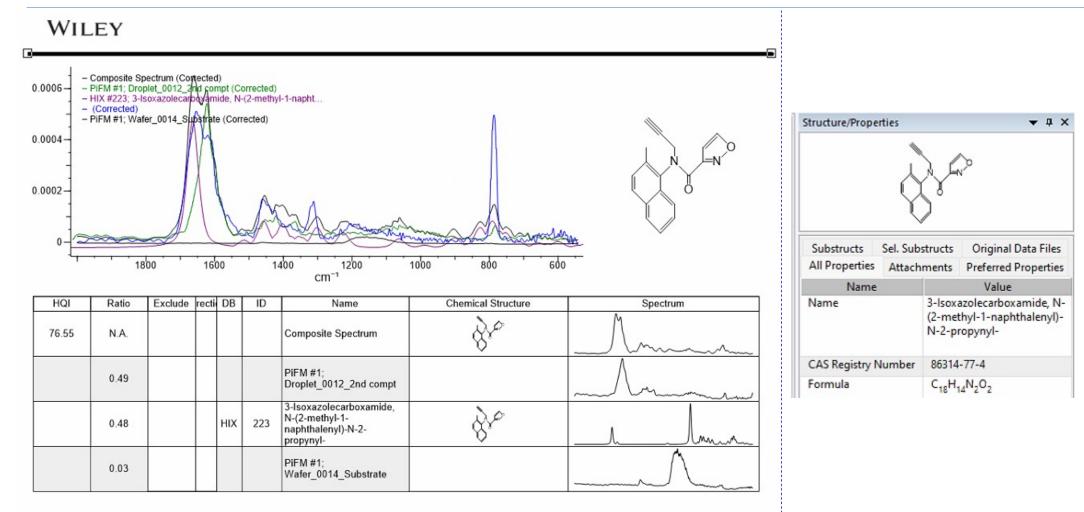


The result of the two components search for the defect 1 is same to the top result of the one component search.

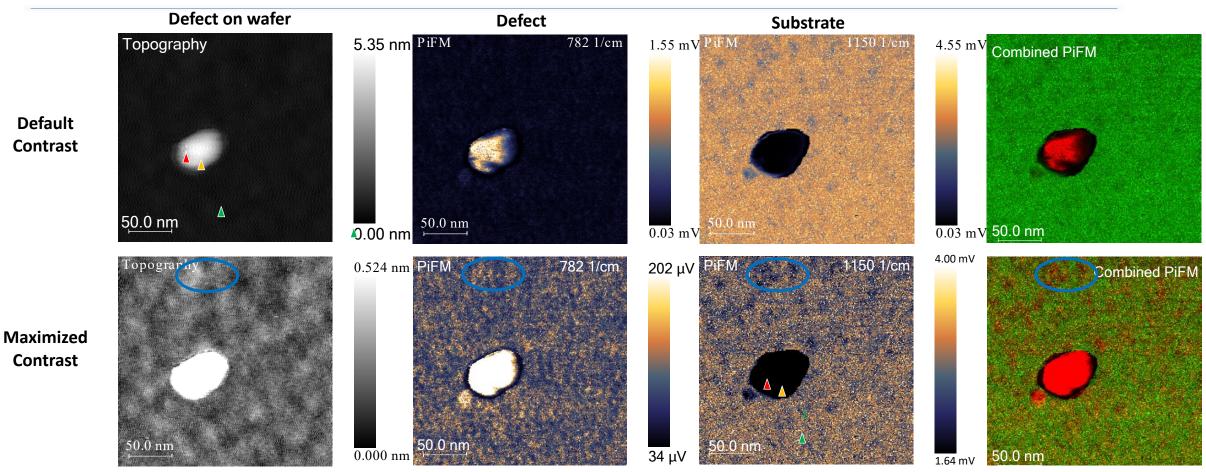
HQI	Ratio	Exclude	recti	DB	ID	Name	Chemical Structure	Spectrum		
65.84	N.A.					Composite Spectrum		And		
	0.92			CFX	1568	CALCIUM OXALATE				
	0.08					PiFM #1; Substrate				



Three Components Search – Defect (gold spectrum)



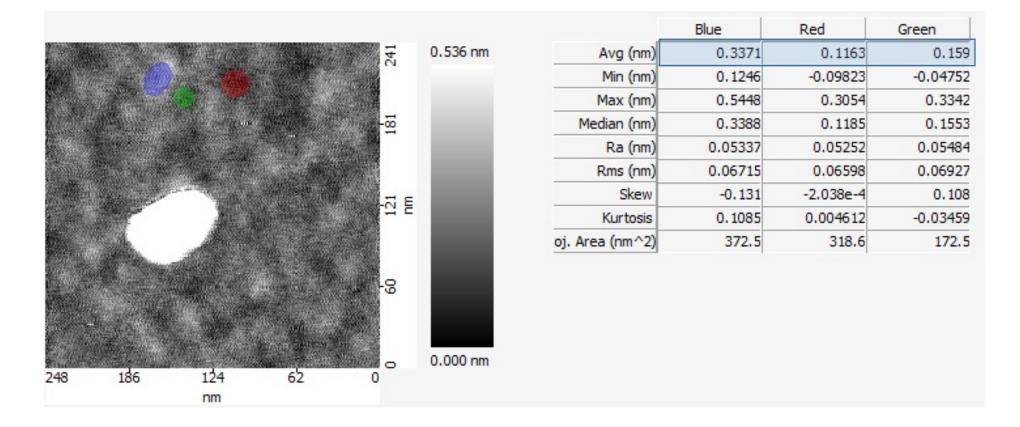
Analysis of Wafer Defect/Residue Processed by Ultrapure Water



The bottom row of images are the same as the top row but the contrast has been maximized to show the PiFM signal variation on the substrate. There are increases in signal at 782 cm⁻¹ on the substrate where 1150 cm⁻¹ decreases, and the topography height also increases slightly (blue circles). This suggests that there are also very thin layers of the defect on the substrate along with the larger defect. IR PiFM is surface sensitive, and any intervening residue between the substrate and the tip will reduce the signal strength of the substrate (in this case 1150 cm⁻¹).



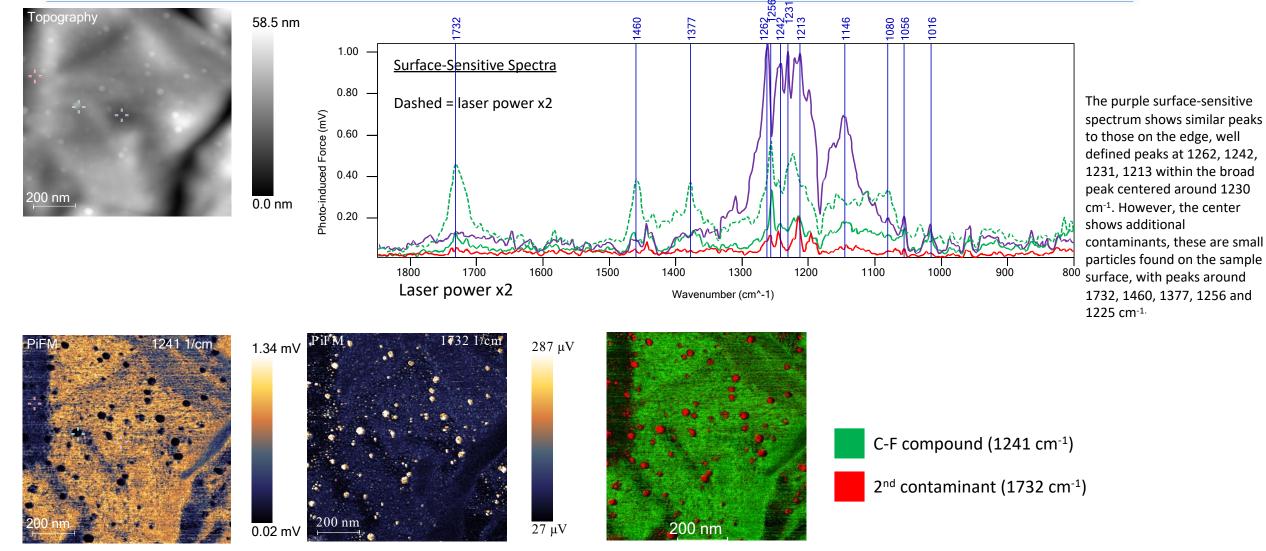
Analysis of Wafer Defect/Residue Processed by Ultrapure Water



The average height of the residue seems to be about 0.2nm thick, which may indicate a monolayer.



Failure of Contact Pad Analyzed: 1 μ m² Topography, PiFM and Spectra

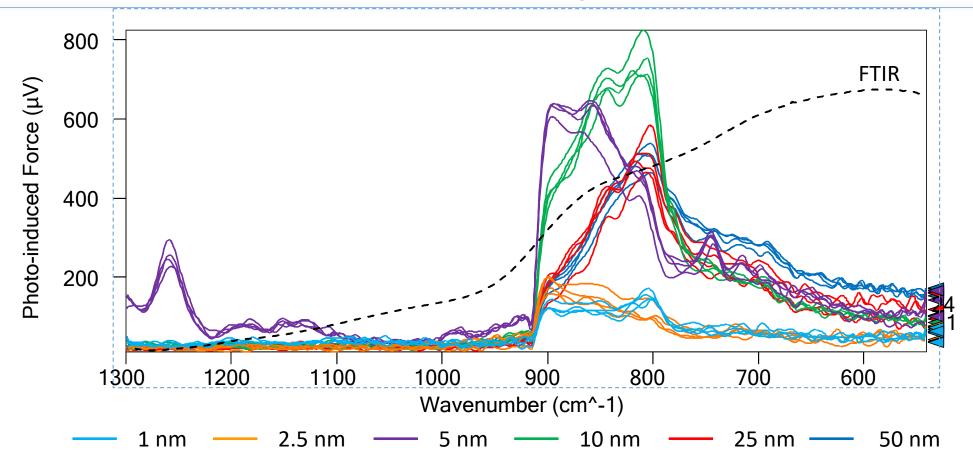




ALD Films



PiF-IR Analysis of ALD Grown Al₂O₃

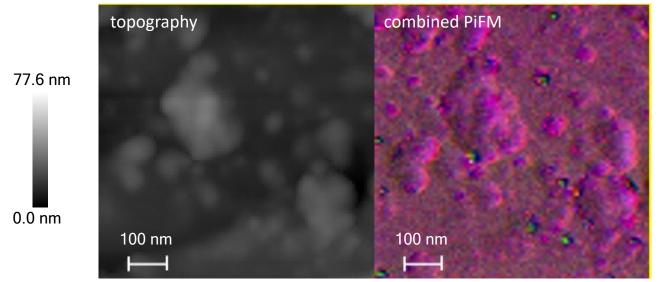


Four spectra (1 μ m spacing) are acquired from each sample; they are reasonably repeatable indicating that each sample is homogeneous. Compared to the broad FTIR spectrum, PiF-IR spectra display sharper features that vary with thickness.



PiFM Image of ALD Grown Al₂O₃

ALD Alumina Substrate



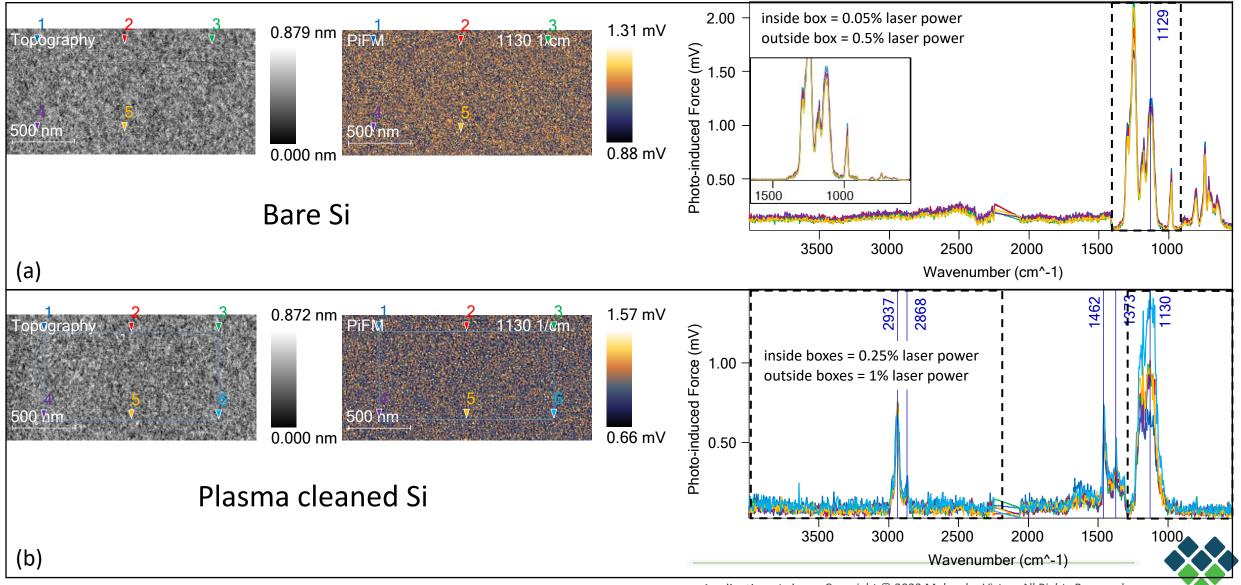
Alumina is grown on top of a substrate material via ALD and examined via IR PiFM. Topography is show on the left. A combined PiFM image consisting of one PiFM image for alumina (purple) and another one for the substrate (green) clearly shows multiple pinholes (~ 10 nm in size) in the alumina layer.



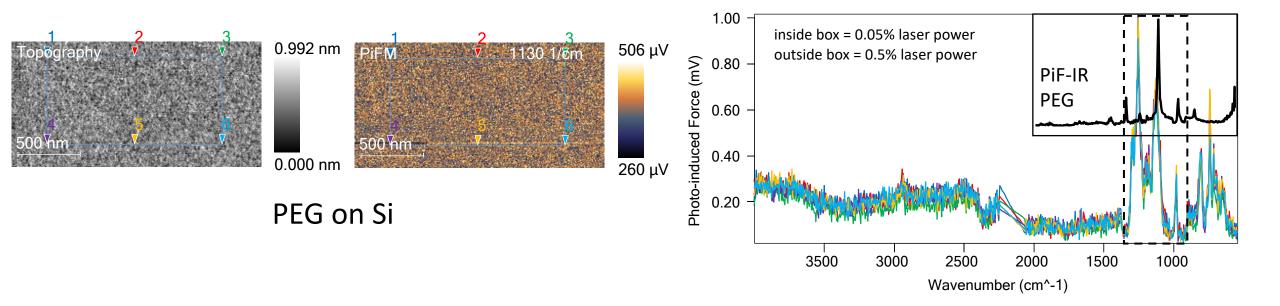
Surface Contaminations and Monolayers



Organic Contaminants on Substrates

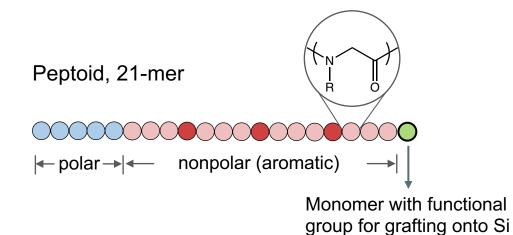


Unsuccessful monolayer of PEG on Si



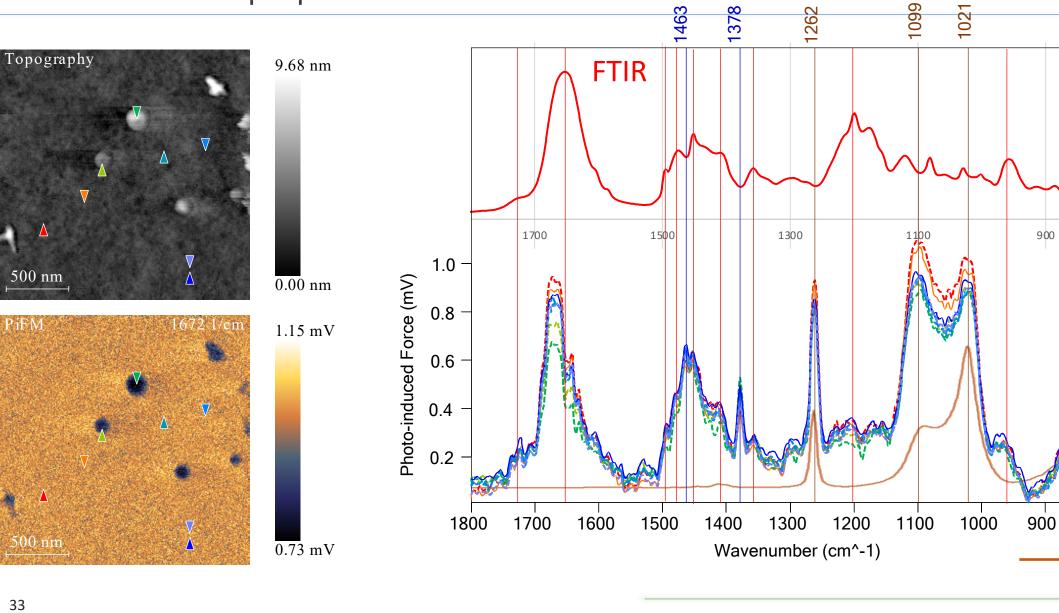


Monolayer of peptoid film





30 nm thick peptoid film



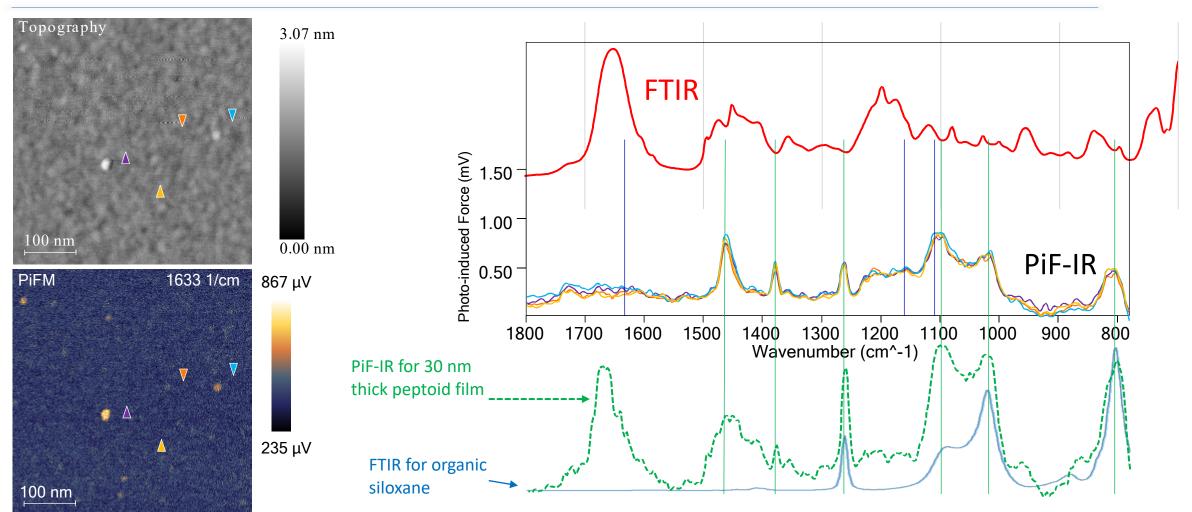
802

800

Siloxane FTIR

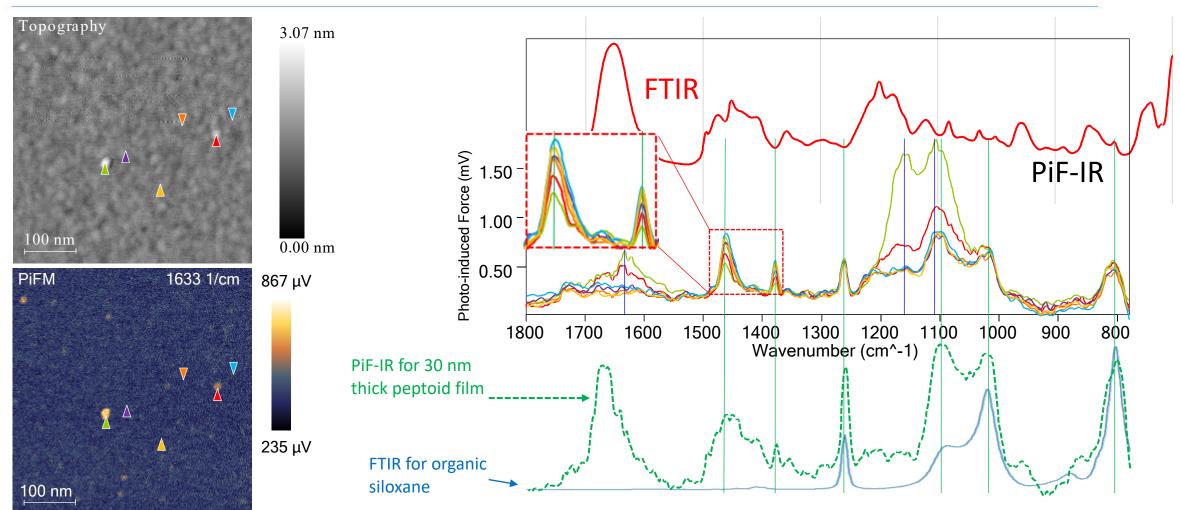
700

"Monolayer" of peptoid molecules





Only fragments of peptoid molecules



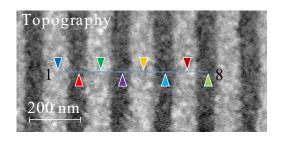
Height: 1.8 nm x Width: 16 nm

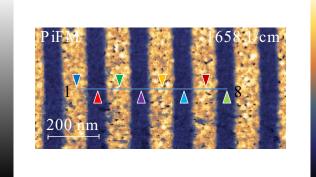
Height: 1.2 nm x Width: 16 nm

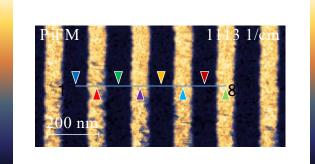
Monolayer of peptoid film patterned via e-beam lithography

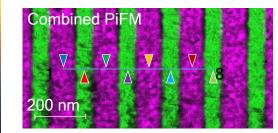
1.15 mV

 $\overline{0.05}$ mV







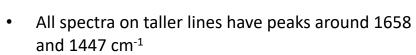


2.44 mV

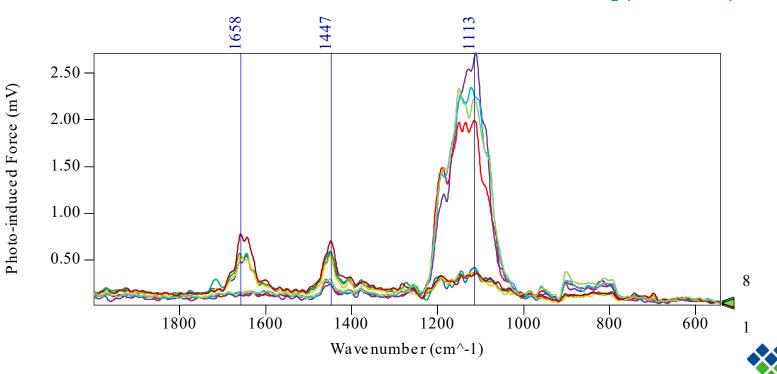
Peptoid (1658 cm⁻¹) 0.03 mV SiO₂ (1113 cm⁻¹)

0.00 nm

2.24 nm



- The spectra on the substrate show strong peak around 1113 cm⁻¹
- Images clearly highlight peptoid lines (1658 cm⁻¹) and substrate (1113 cm⁻¹)

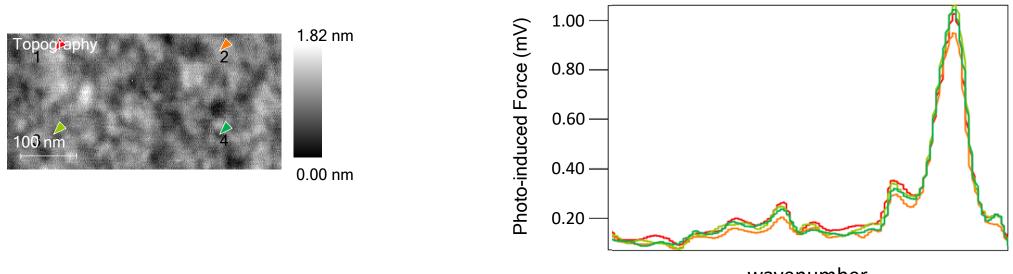


٠

Chemical Metrology of EUV Resist



Multiple PiF-IR Spectra (Repeatability & Variability)

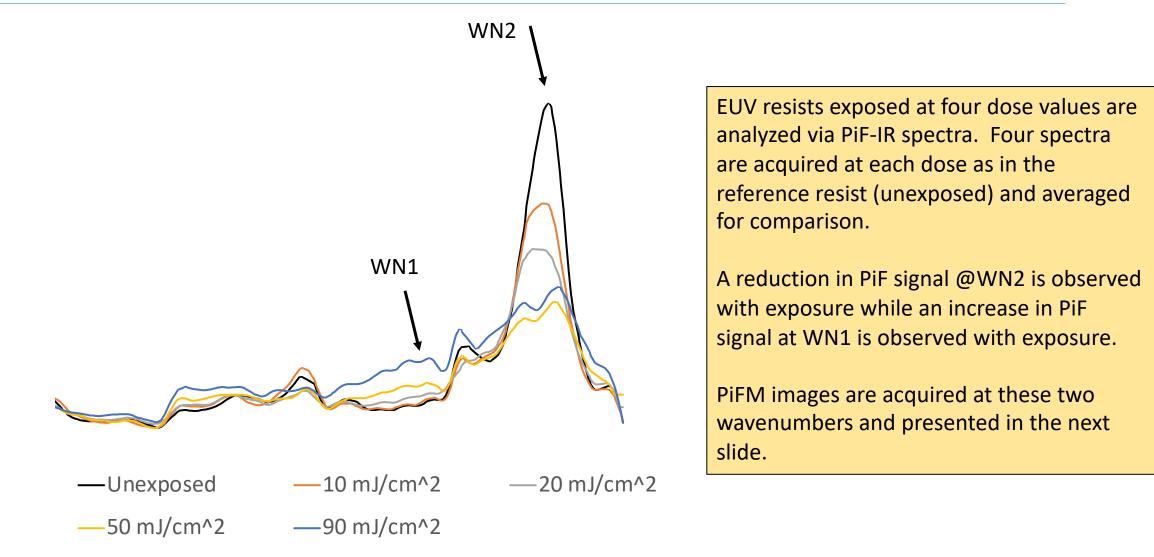


wavenumber

The repeatability of the four PiF-IR spectra at different locations is decent and indicates that the chemical composition of the metal oxide EUV resist is reasonably homogeneous. The values of the wavenumbers are hidden per manufacturer's request.

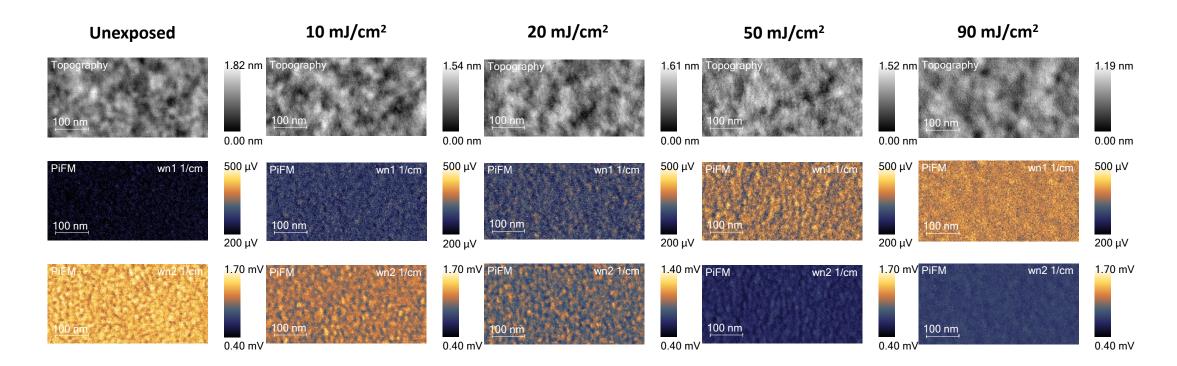


Comparison of Averaged PiF-IR Spectra with Exposure





PiFM Images of Metal Oxide EUV Resist @ Different Exposure

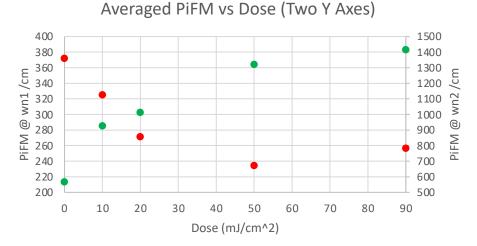


Similar trends are observed in the PiFM images at the two wavenumbers. The intensity at wn2 decreases with dose while the intensity at wn1 increases with dose. For each wavenumber, the same tip with the same laser intensity is used; the display scale is the same as well.



PiFM Signal @ wn1 and wn2 cm⁻¹ vs Dose

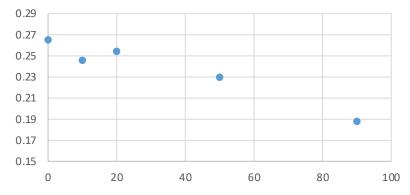
Clear trends are observed at two wavenumbers. The area average of PiF intensity at wn2 decreases with dose while the area average of PiF intensity at wn1 increases with dose. The signal at wn2 suggest that the chemical change upon exposure seems to stall somewhere between 30 and 50 mJ/cm².



• average PiFM signal at wn2 • average PiFM signal at wn1

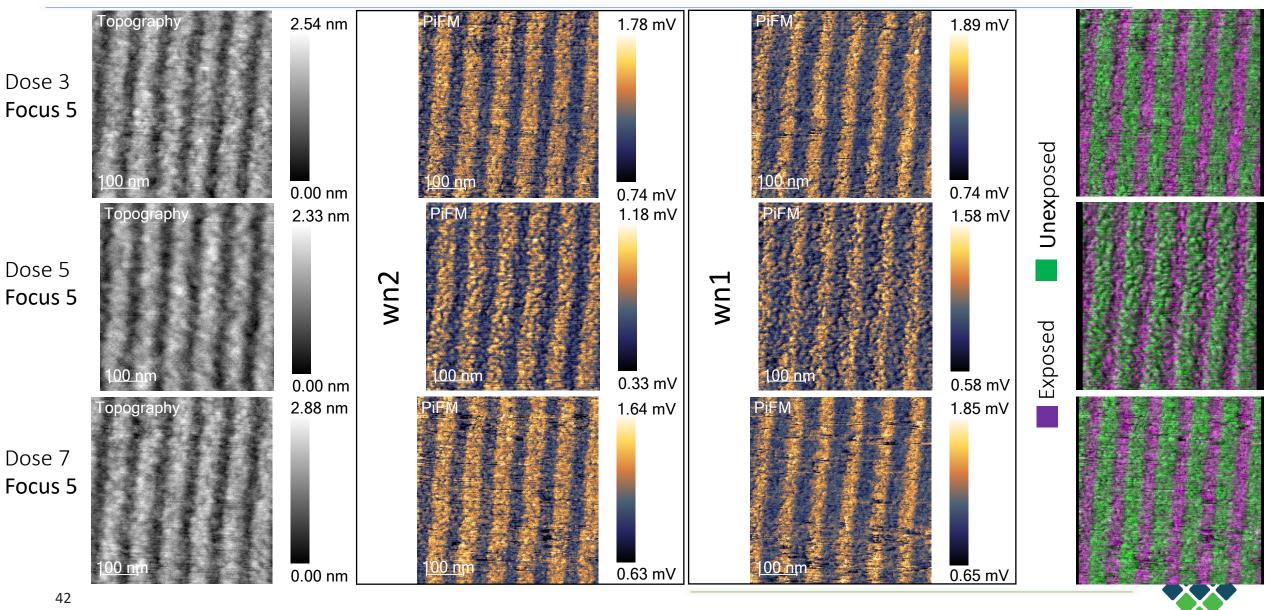
Somewhat similar trend is observed for the rms roughness if one outlier datum is ignored.







Preliminary Results on Patterned MO EUV Resist @ Different Doses



- IR PiFM measures sample's nanoscale infrared absorption via mechanical force detection.
- It achieves sub-5 nm spatial resolution, single-molecule-level sensitivity, orientation discrimination, and ease-of-use.
- It works equally well with both organic and inorganic materials even at nominal thickness of ~ 1 nm.
- For defect analysis, it complements other existing nanoscale analytical tools, which can only provide elemental information.
- Examples of analyzing surface functionalization/contamination, ultrathin ALD films, and latent chemical images of EUV resists have been shared.
- For accurate identification of defects, it is important that the IR spectra database includes the spectra for all material the sample may be exposed to in its processing steps.



Thank you.

www.molecularvista.com info@molecularvista.com



Samples

- Norway spruce Tapani Vuorinen, Aalto University, Finland
- Peptoid Beihang Yu, Lawrence Berkeley Lab, USA
- PCL/AA Phuong Nguyen-Tri, Université du Québec à Trois-Rivières, Canada
- ODTS on SiO₂ Stacey Bent, Stanford University, USA
- Various Substrates Jeff Chinn, IST, USA
- Metal oxide EUV Resist Patrick Naulleau, Lawrence Berkeley Lab, USA





Stay Tuned!

We'll announce the next episode soon on our website at:

https://covalentmetrology.com

Thank you for attending!

To show our appreciation, we're offering all attendees a **special limited-time discount**

Up to 15% Attendee Discount*

On your next PiFM Analysis Request

*10% discount for jobs quoted at \$1,500 - \$2,999; jobs over \$3,000 qualify for the 15% discount

Schedule a Free Discovery Consult Appointment to discuss your needs with a Covalent expert

Calendly Link in the Chat

All Episodes On-Demand in the Covalent Academy



Covalent Academy

Get more from your data by building your knowledge of advanced materials characterization.



Learning Center

Browse All Topics

My Learning

Topics In Progress Completed Topics

Find all our past episodes at

academy.covalentmetrology.com







ACADEM







Q & A Session

48



COVALENT METROLOGY

Thank You